

Title (en)
Multijunction semiconductor device.

Title (de)
Halbleiteranordnung mit mehreren Übergängen.

Title (fr)
Dispositif semi-conducteur à multi-jonction.

Publication
EP 0177864 A2 19860416 (EN)

Application
EP 85112318 A 19850928

Priority
JP 21394484 A 19841011

Abstract (en)
A heat-resistant multijunction semiconductor device comprising a p-layer, an n-layer and a diffusion-blocking layer, the diffusion-blocking layer being provided between the p-layer and the n-layer. The semiconductor device can reduce the fall-down of quality which is caused by the diffusion of dopant atoms in the p-layer and n-layer, respectively, into the other layer.

IPC 1-7
H01L 29/06; **H01L 31/06**

IPC 8 full level
H01L 31/04 (2006.01); **H01L 25/07** (2006.01); **H01L 29/06** (2006.01); **H01L 29/868** (2006.01); **H01L 31/06** (2012.01); **H01L 31/075** (2006.01); **H01L 31/076** (2012.01); **H01L 31/20** (2006.01)

CPC (source: EP KR US)
H01L 25/074 (2013.01 - EP US); **H01L 29/868** (2013.01 - EP US); **H01L 31/076** (2013.01 - EP US); **H01L 31/10** (2013.01 - KR); **H01L 31/202** (2013.01 - EP US); **H01L 2224/32145** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US); **Y02E 10/548** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP US)

Cited by
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DOCDB simple family (publication)
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